

ABSTRACT OF THE DISCLOSURE

There is provided a method for fabricating an image display device having an active matrix substrate including high-performance transistor circuits operating with high mobility as drive circuits for driving pixel portions which are arranged as a matrix. The portion of a polysilicon film formed in a drive circuit region DAR1 provided on the periphery of the pixel region PAR of the active matrix substrate SUB1 composing the image display device is irradiated and scanned with a pulse modulated laser beam or a pseudo CW laser beam to be reformed into a quasi-strip-like-crystal silicon film having a crystal boundary continuous in the scanning direction so that discrete reformed regions each composed of the quasi-strip-like-crystal silicon film are formed. In virtual tiles TL composed of the discrete reformed regions, drive circuits having active elements such as thin-film transistors or the like are formed such that the channel directions thereof coincide with the direction of crystal growth in the quasi-strip-like-crystal silicon film.